

Inventor: Luan C. Tran
Title: Methods of Forming Semiconductor Constructions
Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 10/364,054, filed February 10, 2003. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated:

July 21, 2003

By:

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Reg. No. 48,711

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				ATTY. DOCKET NO. MI22-2358	priority SERIAL NO. 10/364,054		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Luan C. Tran			
				priority FILING DATE February 10, 2003	priority GROUP 2812		
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,458,666 B2	10-2002	Wasshuber			
	AB	6,444,548 B2	09-2002	Divakaruni et al.			
	AC	3,886,003	05-1975	Takagi et al.			
	AD	4,366,338	12-1982	Turner et al.			
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	AF	6,506,647 B2	01-2003	Kuroda et al.			
	AG	US2001/0036713A1	11-01-2001	Rodder et al.			July 5, 2001
	AH	US2002/0034865A1	03-21-2002	Umimoto et al.			Nov. 30, 2001
	AI	09/876,722		Scott			June 6, 2001
	AJ	10/133,193		McQueen et al.			April 26, 2002
	AK						
	AL						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AM						
	AN						
	AO						
	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AQ		Young et al., "A 0.13 μm CMOS Technology with 193 nm Lithography and Cu/Low-k for High Performance Applications", IEDM, pgs. 563-566, April 2000.				
	AR		Yeh et al., "Optimum Halo Structure for Sub-0.1 μm CMOSFETs", IEEE Transactions on Electronic Devices, Vol. 48, No. 10, October 2001, pgs. 2357-2362.				
	AS		Bouillon et al., "Re-examination of Indium implantation for a low power 0.1 μm technology". IDEM, pgs. 897-900, 1995 (year is sufficient so that date is not in issue).				
EXAMINER				DATE CONSIDERED			
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							